

BP15L50SP

Schottky Barrier Diode

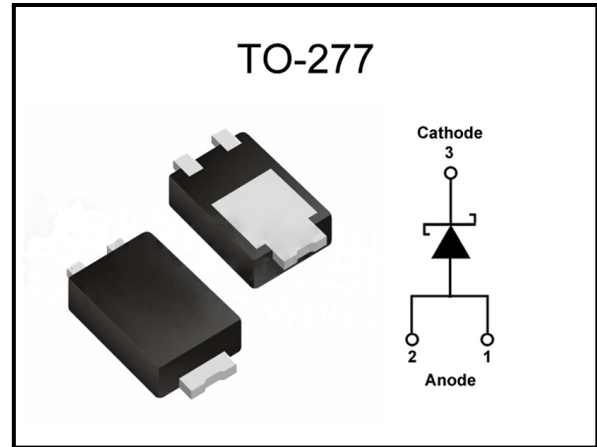
Features

- Low forward voltage drop
- High current capability
- High reliability
- High surge current capability

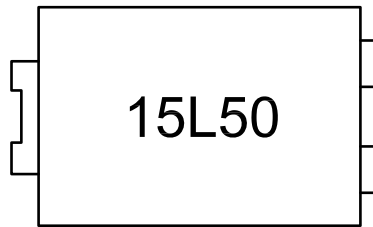
Description

- Case: molded plastic
- Polarity: Color band denotes cathode
- Package: TO-277 Plastic Package

Package



Marking



Ordering information

Order code	Package	Marking	Base qty	Delivery mode
BP15L50SP	TO-277	15L50	5K	Tape and reel

Maximum Ratings @T_A=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Limit	Unit
V _{RRM}	Maximum Repetitive Peak Reverse Voltage	–	50	V
I _{F(AV)}	Maximum Average Forward Rectified Current	–	15	A
I _{FSM}	Peak forward surge current 8.3ms single half sine-wave superimposed on rated load per diode	–	280	A
T _J ,T _{STG}	Operating Junction and Storage Temperature Range	–	-40 to +150	°C
R _{θJA}	Typical Thermal Resistance per diode (Mounted on FR-4 PCB)	–	72	°C/W



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Electrical Characteristics @T_A=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Limit		Unit
			Typ.	Max.	
V _F	Instantaneous Forward Voltage Per Diode	I _F =5A, T _J =25°C	0.40	–	V
		I _F =15A, T _J =25°C	0.48	0.52	
		I _F =5A, T _J =125°C	0.29	–	
		I _F =15A, T _J =125°C	0.39	–	
I _R	Instantaneous Reverse Current Per Diode at Rated Reverse Voltage	T _J =25°C	20	60	uA
		T _J =125°C	–	30	mA



Typical Performance Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise noted)

Figure 1: Forward Voltage Characteristics

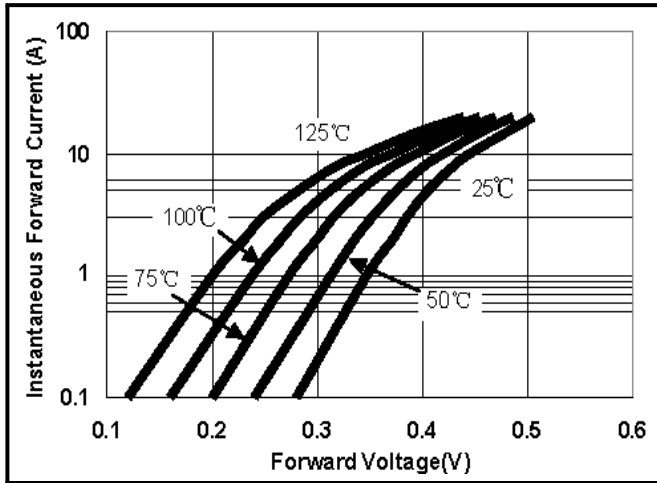


Figure 2: Reverse Leakage Characteristics

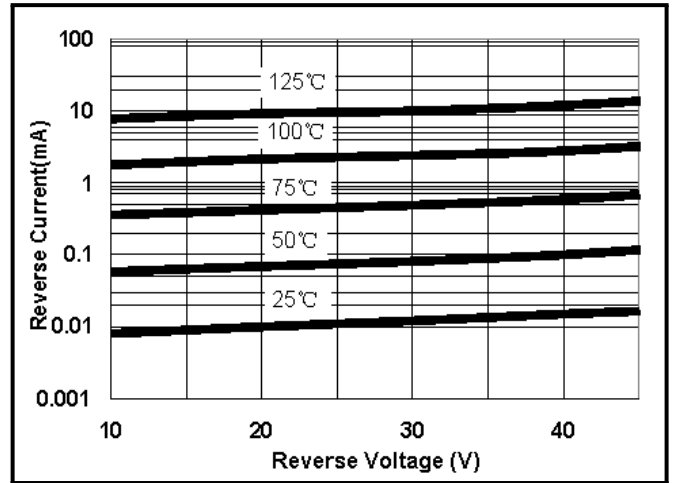


Figure 3: Junction Capacitance Characteristics

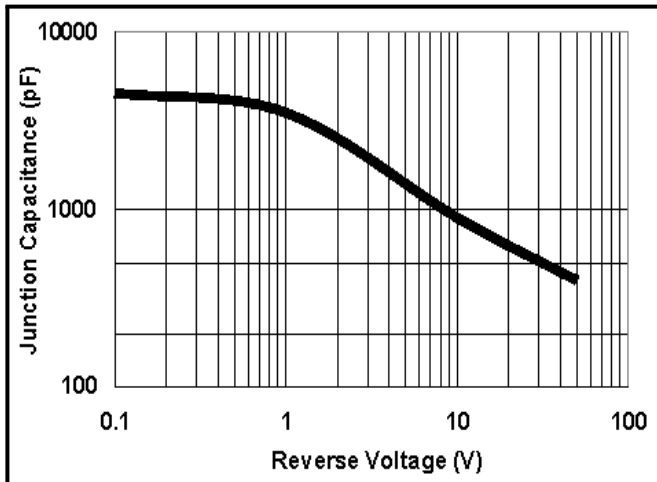
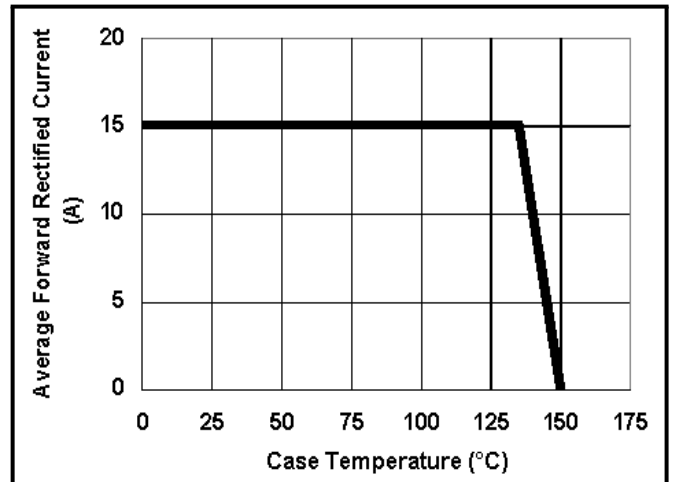


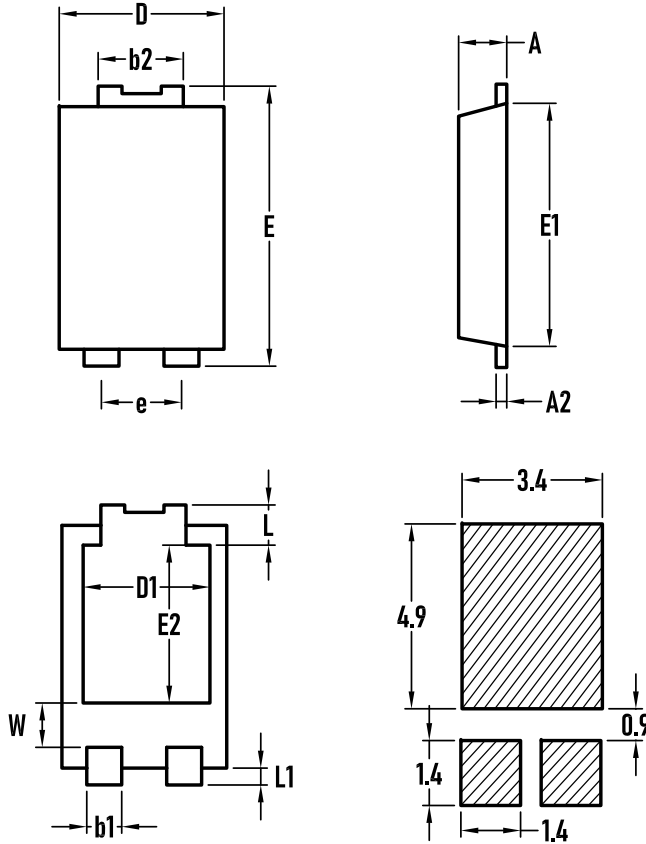
Figure 4: Forward Current Derating Curve



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Outline Drawing - TO-277



SYMBOL	MILLIMETER	
	MIN.	MAX.
A	1.1	1.3
A2	0.3	0.4
b1	0.8	1
b2	1.7	1.9
D	3.9	4.1
D1	3.054	
E	6.4	6.6
e	1.84	
E1	5.3	5.5
E2	3.549	
L	0.8	1
L1	0.5	0.7
W	1.1	1.4

